

What is claimed is:

1. A method of preparing a carbon-doped group III-V compound semiconductor crystal, comprising the steps of:

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placing a compound raw material, solid carbon, and a boron oxide substance into a crucible or a boat,

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sealing said crucible or boat containing said compound raw material, said solid carbon, and said boron oxide substance within an airtight vessel formed of a gas impermeable material,

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heating and melting said compound raw material in said crucible or said boat sealed within said airtight vessel, and

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solidifying said melted compound raw material to grow a carbon-doped compound semiconductor crystal,

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wherein an amount of said solid carbon placed into said crucible or said boat is larger than an amount of carbon doped into said compound semiconductor crystal.

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2. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, further comprising a step of heating and melting said boron oxide substance and having said melted boron oxide substance in contact with at least a portion of said solid carbon, during said step of heating and melting said compound raw material.

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3. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said gas impermeable material comprises a material selected from the group consisting of quartz and pBN.

4. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said boron oxide substance comprises boron oxide and water.

5 5. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 4, wherein said boron oxide substance contains 10-500 wt ppm of said water.

10 6. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said amount of said solid carbon placed into said crucible or said boat is at least 10 times larger than said amount of carbon doped into said compound semiconductor crystal.

15 7. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, further comprising a step of subjecting said solid carbon to a heat treatment under reduced pressure before placing said solid carbon into said crucible or said boat.

20 8. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 7, comprising carrying out said heat treatment for 1 hour to 12 hours at a temperature of 500° C. - 2000° C. under a pressure of 1 Torr - 1×10^{-8} Torr.

25 9. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, further comprising a step of maintaining said melted compound raw material in a melted state for a certain time period before said step of solidifying said melted raw material to grow said crystal.

30 10. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 9, wherein said step of maintaining said melted compound raw material in a melted state is carried out for 3-72 hours.

11. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said solid carbon comprises powder carbon.

5 12. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 11, wherein said powder carbon has a grain size of not more than 100 μm .

10 13. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said solid carbon comprises fiber carbon.

15 14. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 13, wherein said fiber carbon has an average diameter of not more than 50 μm .

20 15. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said solid carbon comprises bulk carbon.

25 16. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 15, wherein said bulk carbon has a disk shape with a disk diameter smaller than an inner diameter of said crucible.

30 17. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 15, wherein said bulk carbon comprises a sintered compact of carbon powder.

18. A method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said crucible or said boat comprises pBN.

19. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, wherein said compound raw material comprises GaAs, and wherein said compound semiconductor crystal comprises a GaAs crystal.

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20. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 2, further comprising having said melted boron oxide substance in contact with at least a portion of said melted compound raw material, during said step of heating and melting said compound raw material.

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21. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, further comprising selecting a target amount of said carbon to be doped into said compound semiconductor crystal, and adjusting said amount of said solid carbon placed into said crucible or said boat so as to responsively achieve said target amount of said carbon to be doped into said semiconductor crystal.

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22. The method of preparing a carbon-doped group III-V compound semiconductor crystal according to claim 1, carried out such that said carbon-doped compound semiconductor crystal has a variation of carbon concentration of not more than 8 1/3% between a lowest carbon concentration and a highest carbon concentration, relative to said lowest carbon concentration.

23. A charge for use in vertical boat growth of GaAs single crystal ingots comprising: poly-crystal GaAs material; a source of carbon; and Boron Oxide wherein said source of carbon comprises carbon powder; the nominal doping potential of said carbon powder included in the charge is large compared to the planned target level of carbon dopant in an as grown ingot, and said Boron Oxide is provided in an amount for providing spacer material between an as grown ingot and a crucible wall, and between a seed crystal and the bottom of said crucible.

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24. A charge in accordance with claim 23 wherein the nominal doping potential of said carbon powder included in the charge is the order of 100 times the planned target level of carbon dopant in an as grown ingot.

5 25. A charge in accordance with claim 23 wherein the nominal doping potential of said carbon powder included in the charge is at least several times the planned target level of carbon dopant in an as grown ingot.

10 26. Vertical boat growth of single crystal, semi-insulating GaAs ingots having controlled planned target levels of Carbon therein comprising: (a) loading a crucible with a charge of poly-crystal GaAs material; a source of carbon; and Boron Oxide over a selectively oriented seed crystal; (b) placing said crucible in a closed quartz tube; (c) applying a controlled pattern of heating to melt the charge and a portion of the seed crystal to sequentially freeze the melt starting at the interface with the seed crystal to form a single crystal; wherein said source of carbon is carbon powder in a selected quantity having a defined large nominal doping potential compared to the planned target level of Carbon in an as grown ingot; and said Boron Oxide is provided in an amount for providing spacer material between an as grown ingot and a crucible wall, and between a seed crystal and the bottom of said crucible.

20 27. Vertical boat growth of single crystal, semi-insulating GaAs ingots in accordance with claim 26 wherein said pattern of heating comprises: heating said charge to the melting point temperature of GaAs; holding that temperature for a period of time.

25 28. Vertical boat growth of single crystal, semi-insulating GaAs ingots in accordance with claim 26 wherein the nominal doping potential of said carbon powder included in the charge is the order of 100 times the planned target level of carbon dopant in an as grown ingot.

30 29. Vertical boat growth of single crystal, semi-insulating GaAs ingots in accordance with claim 26 wherein the nominal doping potential of said carbon powder

included in the charge is at least several times the planned target level of carbon dopant in
an as grown ingot.

5 30. Semi-insulating mono crystalline GaAs material produced in accordance with
any of claims 26, 27, 28 or 29.

10 31. The method of any of claims 1 - 22 wherein sufficient boron oxide substance
is placed in said crucible or boat so that the boron oxide substance surrounds the melted
semiconductor compound.

15 32. The method of claim 31 wherein said melting and solidifying is conducted in
a vertical furnace.

20 33. The method of any of claims 1 - 22 wherein said melting and solidifying is
conducted in a vertical furnace.

25 34. The method of any of claims 2 - 10 or 18 - 22 wherein said solid carbon is
powdered carbon.

30 35. The method of claim 34 wherein sufficient boron oxide substance is placed in
said crucible or boat so that the boron oxide substance surrounds the melted
semiconductor compound.

35 36. The method of claim 34 wherein said melting and solidifying is conducted in
a vertical furnace.

40 37. The method of any of claims 2 - 10 or 18 - 22 wherein said solid carbon is
carbon fibers.

45 38. The method of claim 37 wherein sufficient boron oxide substance is placed in
said crucible or boat so that the boron oxide substance surrounds the melted

semiconductor compound.

39. The method of claim 37 wherein said melting and solidifying is conducted in
a vertical furnace.

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